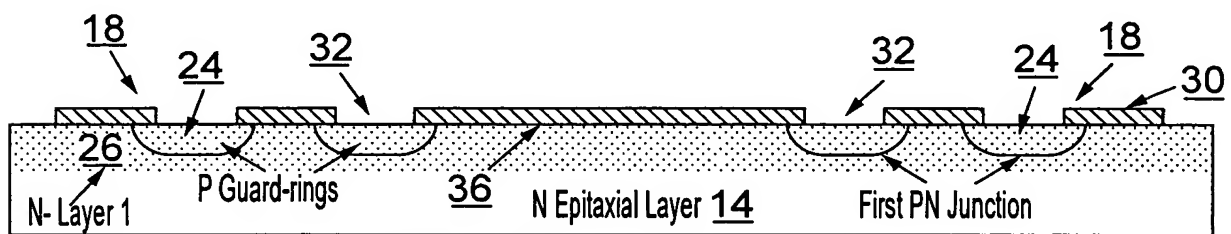
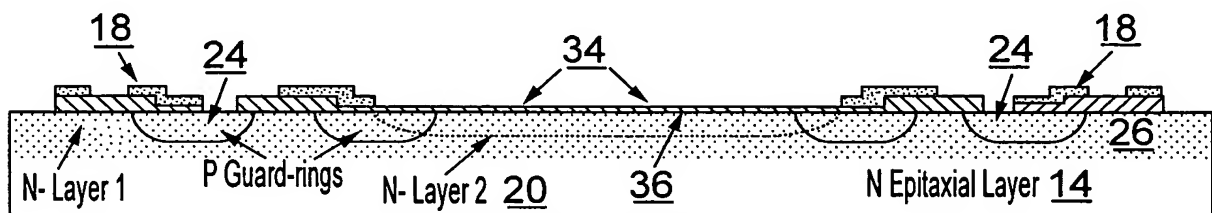


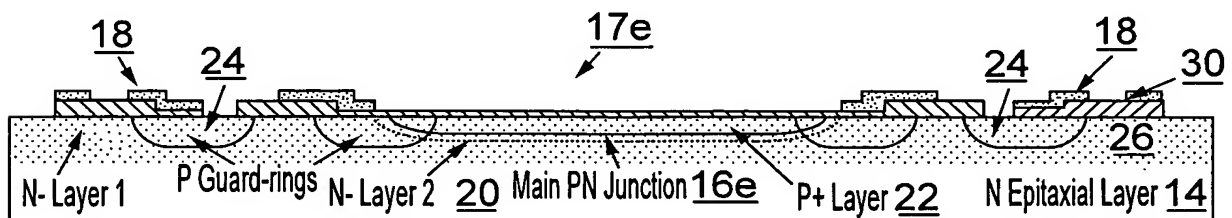
a) Optional N-layer implant over entire wafer.



b) Pattern and diffuse guard-ring boron and optional N-Layer.



c) N-layer implant and diffusion in active area.



d) Shallow P layer implant and diffusion in active area.

FIG. 5